Table S1 Structural and electrical properties of synthesized mesoporous ATO thin films. Average thickness was determined by stylus profiler. *d*-spacing was calculated from GI-SAXS (in-plane) profile. Sheet resistance and resistivity were measured by four-probe method.

Sample	Average Thickness (nm)	Sheet Resistance (kΩ/□)	Resistivity (Ω cm)	d-spacing (nm)
ATO_5_600	123.65	1.92	2.35×10^{-2}	_
ATO_10_600	254.57	4.23	1.02×10^{-1}	_
ATO_20_600	294.78	23.26	6.78×10 ⁻¹	_
ATO_30_600	276.91	41.68	1.11×10^{0}	_
ATO_40_600	217.93	17.53	3.70×10^{-1}	36.1
ATO_50_600	175.85	7.86	1.32×10^{-1}	30.7
ATO_60_600	179.35	6.34	1.08×10^{-1}	30.7
ATO_70_600	174.66	6.64	1.14 × 10 ⁻¹	29.2
ATO_5_800	117.59	1.19	1.29 × 10 ⁻²	_
ATO_10_800	256.46	5.68	1.41 × 10 ⁻¹	_
ATO_20_800	284.44	21.02	5.97×10^{-1}	_
ATO_30_800	221.81	46.95	9.98 × 10 ⁻¹	_
ATO_40_800	201.33	16.65	3.32×10^{-1}	_
ATO_50_800	160.78	5.35	8.04 × 10 ⁻²	34.1
ATO_60_800	170.22	4.91	7.66×10^{-2}	32.2
ATO_70_800	160.79	4.51	6.43 × 10 ⁻²	32.2



Figure S1 Low-magnified SEM images of (a) ATO_5_600 and (b) ATO_10_600.



Figure S2 Top-view SEM images of (a) ATO_5_800, (b) ATO_10_800, (c) ATO_30_800, (d) ATO_50_800 and magnified SEM images of (e) ATO_5_800, (f) ATO_10_800, (g) ATO_30_800, and (h) ATO_50_800.



50 nm

Figure S3. Dark field SEM image and EDS elemental mapping of ATO_50_600.



Figure S4. Enlarged image of high-magnified TEM image of ATO_50_600 (Figure 2b).